

ISHAY

Wideband/Video "T" Switches

DESCRIPTION

The DG540, DG541, DG542 are high performance monolithic wideband/video switches designed for switching RF, video and digital signals. By utilizing a "T" switch configuration on each channel, these devices achieve exceptionally low crosstalk and high off-isolation. The crosstalk and off-isolation of the DG540 are further improved by the introduction of extra GND pins between signal pins.

To achieve TTL compatibility, low channel capacitances and fast switching times, the DG540 family is built on the Vishay Siliconix proprietary D/CMOS process. Each switch conducts equally well in both directions when on.

FEATURES

- Halogen-free according to IEC 61249-2-21 Definition
- Wide Bandwidth: 500 MHZ
- Low Crosstalk: 85 dB
- High Off-Isolation: 80 dB at 5 MHz
- "T" Switch Configuration
- TTL and CMOS Logic Compatible
- Fast Switching t_{ON}: 45 ns
- Low R_{DS(on)}: 30 Ω
- Compliant to RoHS Directive 2002/95/EC

BENEFITS

- Flat Frequency Response ٠
- High Color Fidelity
- Low Insertion Loss
- Improved System Performance
- **Reduced Board Space**
- **Reduced Power Consumption**
- Improved Data Throughput

APPLICATIONS

- RF and Video Switching
- **RGB** Switching
- Local and Wide Area Networks
- Video Routing
- Fast Data Acquisition
- ATE
- Radar/FLR Systems
- Video Multiplexing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



| TRUTH TABLE | | | | |
|-------------|--|--|--|--|
| Switch | | | | |
| OFF | | | | |
| ON | | | | |
| | | | | |

Logic "0" \leq 0.8 V Logic "1" ≥ 2 V



RoHS COMPLIANT HALOGEN FREE

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| TRUTH TABLE - DG541 | | | | |
|---------------------|--------|--|--|--|
| Logic | Switch | | | |
| 0 | OFF | | | |
| 1 | ON | | | |
| Logic "0" ≤ 0.8 V | | | | |

 Logic
 SW1, SW2
 SW3, SW4

 0
 OFF
 ON

 1
 ON
 OFF

 Logic "0" ≤ 0.8 V
 V

Logic "1" ≥ 2 V

| ORDERING INFORMATION | | | | | |
|----------------------|---------------------|-------------------------------|--|--|--|
| Temp Range | Package Part Number | | | | |
| DG540 | · | | | | |
| - 40 to 85 °C | 20-Pin Plastic DIP | DG540DJ-E3 | | | |
| - 40 10 65 0 | 20-Pin PLCC | DG540DN-E3 | | | |
| - 55 to 125 °C | 00 Din Sidebraza | DG540AP | | | |
| - 55 10 125 10 | 20-Pin Sidebraze | DG540AP/883 | | | |
| DG541 | | | | | |
| - 40 to 85 °C | 16-Pin Plastic DIP | DG541DJ-E3 | | | |
| - 40 10 65 0 | 16-Pin Narrow SOIC | DG541DY-T1-E3 | | | |
| - 55 to 125 °C | 16-Pin Sidebraze | DG541AP | | | |
| - 55 10 125 10 | To-Pill Sidebraze | DG541AP/883, 5962-9076401MEA | | | |
| DG542 | | | | | |
| - 40 to 85 °C | 16-Pin Plastic DIP | DG542DJ-E3 | | | |
| - 40 10 05 0 | 16-Pin Narrow SOIC | DG542DY-T1-E3 | | | |
| - 55 to 125 °C | 16-Pin Sidebraze | DG542AP | | | |
| - 55 10 125 0 | TO-FITI SIDEDIAZE | DG542AP/883, 5962-91555201MEA | | | |

DG542

Logic "1" \ge 2 V



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| | Parameter | Symbol | Limit | Unit |
|--|--|--------|--|------|
| V+ to V- | | | - 0.3 to 21 | |
| V+ to GND | | | - 0.3 to 21 | |
| V- to GND | | | - 19 to + 0.3 | |
| Digital Inputs | | | (V-) - 0.3 to (V+) + 0.3 or 20 mA, whichever occurs first | V |
| V _S , V _D | | | (V-) - 0.3 to (V+) + 14 or 20 mA, whichever occurs first | |
| Continuous Current (Any Termi | urrent (Any Terminal) 2 | | 20 | mA |
| Current, S or D (Pulsed at 1 ms | s, 10 % duty cycle max) | | 40 | ША |
| Storage Temperature | (AP Suffix) | | - 65 to 150 | °C |
| Storage Temperature | (DJ, DN, DY Suffixes) | | - 65 to 125 | C |
| | 16-Pin Plastic DIP ^b | | 470 | |
| Power Dissipation (Package) ^a | 20-Pin Plastic DIP ^c | | 800 | |
| | 16-Pin Narrow Body SOIC ^d | | 640 | mW |
| | 20-Pin PLCC ^d | | 800 | |
| | 16-, 20-Pin Sidebraze DIP ^e | | 900 | |

Notes:

a. All leads welded or soldered to PC Board.

b. Derate 6.5 mW/°C above 25 °C.

c. Derate 7 mW/°C above 25 °C.

d. Derate 10 mW/°C above 75 °C.

e. Derate 12 mW/°C above 75 °C.

SCHEMATIC DIAGRAM (typical channel)



Figure 1.

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| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | SPECIFICATIONS ^a | | | | | | | | | | |
|---|---|-----------------------|---|------------|--------------------|-------------------|-------|-------------------|-------------------|-------------------|------|
| $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | | | Unless Specifie | ed | | | | | | | |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | | | | | h | | 4 | | F | F | |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | | Symbol | $V_{\rm INH} = 2$ V, $V_{\rm INL} = 0$ |).8 V' | Temp. ^D | Тур. ^с | Min.ª | Max. ^a | Min. ^a | Max. ^a | Unit |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | ÷ | 1 | Γ | | 1 | I | | l | 1 | 1 | |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | | V _{ANALOG} | V- = - 5 V, V+ = | 12 | - | | - 5 | - | - 5 | - | V |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | On-Resistance | | I _S = - 10 mA, V _D = | = 0 V | | | | 100 | | 75 | Ω |
| | R _{DS(on)} Match | $\Delta R_{DS(on)}$ | | | Room | 2 | | - | | - | |
| $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | Source Off Leakage Current | I _{S(off)} | $V_{\rm S} = 0 \rm V, V_{\rm D} = 10$ | 0 V | | - 0.05 | - 500 | 500 | - 100 | 100 | |
| $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | Drain Off Leakage Current | I _{D(off)} | $V_{\rm S} = 10 \ {\rm V}, \ {\rm V}_{\rm D} = 0$ | 0 V | Full | - 0.05 | - 500 | 500 | - 100 | 100 | nA |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | Channel On Leakage Current | I _{D(on)} | $V_{S} = V_{D} = 0 V$ | , | | - 0.05 | | | | | |
| $\begin{array}{c c c c c c c c c c c c c c c c c c c $ | Digital Control | | | | | | | | | | |
| $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$ | Input Voltage High | | | | Full | | 2 | | 2 | | v |
| $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | Input Voltage Low | V _{INL} | | | Full | | | 0.8 | | 0.8 | v |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | Input Current | I _{IN} | V _{IN} = GND or V | ' + | | 0.05 | | | | | μA |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | Dynamic Characteristics | | | | | | | | | | |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | On State Input Capacitance ^e | C _{S(on)} | $V_{\rm S} = V_{\rm D} = 0 V$ | , | Room | 14 | | 20 | | 20 | |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | Off State Input Capacitance ^e | | V _S = 0 V | | Room | 2 | | 4 | | 4 | pF |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | Off State Output Capacitance ^e | C _{D(off)} | V _D = 0 V | | Room | 2 | | 4 | | 4 | 1 |
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | Bandwidth | | $R_L = 50 \Omega$, See Fig | gure 5 | Room | 500 | | | | | MHz |
| $\begin{array}{c c c c c c c c c c c c c c c c c c c $ | Turn On Time | t | | | | 45 | | | | - | |
| $ \begin{array}{cccccccccccccccccccccccccccccccccccc$ | ium-on nine | LON | _ | DG542 | | 55 | | | | | ne |
| $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | | torr | | | | 20 | | | | | 115 |
| $\begin{array}{c c c c c c c c c c c c c c c c c c c $ | | OFF | | | | 25 | | | | | |
| Off IsolationOIRRImage: General conditionDGS Hz f = 5 MHz DG541DG541Room Room- 60Image: General conditionMage: General conditionGeneral conditionGeneral conditionMage: General condition <td>Charge Injection</td> <td>Q</td> <td></td> <td>= 0 V</td> <td>Room</td> <td>- 25</td> <td></td> <td></td> <td></td> <td></td> <td>рС</td> | Charge Injection | Q | | = 0 V | Room | - 25 | | | | | рС |
| See Figure 4DG542Room- 75Image: Constant of the set of th | | | $R_{IN} = 75 \Omega, R_L = 75 \Omega$ | DG540 | Room | - 80 | | | | | |
| All Hostile Crosstalk $X_{TALK(AH)}$ $R_{IN} = 10 \Omega, R_L = 75 \Omega$ f = 5 MHz, See Figure 6 Room - 85 Image: Constraint of the second se | Off Isolation | OIRR | f = 5 MHz | | Room | - 60 | | | | | |
| All Hostile Crosstalk $\Lambda_{TALK(AH)}$ $f = 5$ MHz, See Figure 6 Hoom -85 Image: Constraint of the second se | | | See Figure 4 | DG542 | Room | - 75 | | | | | dB |
| Positive Supply Current I+ All Channels On or Off Room 3.5 6 6 Full Boom - 3.2 - 6 - 6 | All Hostile Crosstalk | X _{TALK(AH)} | | | Room | - 85 | | | | | |
| Positive Supply Current I+ All Channels On or Off Full 9 9 9 mA Negative Supply Current I- All Channels On or Off Room - 3.2 - 6 - 6 mA | Power Supplies | | · | | | | | | | | |
| Negative Supply Current | Positive Supply Current | l+ | All Channels On a | r Off | | 3.5 | | | | | m A |
| | Negative Supply Current | I- | | | | - 3.2 | | | | | |

Notes:

a. Refer to PROCESS OPTION FLOWCHART .

b. Room = 25 $^{\circ}\text{C},$ full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

e. Guaranteed by design, not subject to production test.

f. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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DG540, DG541, DG542 Vishay Siliconix

100

= - 5 V v.

V- = - 3 V

125

TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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100

5

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)





Operating Supply Voltage Range

- 4

- 5

- 3

V- - Negative Supply (V)

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- 6

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10

0

- 1

- 2

Figure 5. Bandwidth

+ 15 V С V+ Vo D s ٧s റ \sim Rg $= 75 \Omega$ R_L 75 Ω ξ IN 0 V, 2.4 V 0 GND V. С Q - 3 V V_{S} Off Isolation = 20 log Vo C = RF Bypass Figure 4. Off Isolation

 ΔV_O = measured voltage error due to charge injection The charge injection in coulombs is $\Delta Q = C_L \times DV_Q$

+ 15 V

V.

Ò

- 3 V

D

Q

V+

OFF

 ΔV_{O}





٧₀

 IN_{X}

C

 $R_g = 50 \ \Omega$

0 V, 2.4 V O

s

IN

GND

ON

TEST CIRCUITS

Rg

3 V

л

Vg

VISHAY



+ 15 V

D ٠.

V-

δ - 3 V 0 Vo

C_L 1000 pF

V+

 \sim

s

IN

GND

_



DG540, DG541, DG542

Vishay Siliconix

ON

 V_{O}

0

R_L 50 Ω

Ş

С

Vishay Siliconix

TEST CIRCUITS



Figure 6. All Hostile Crosstalk

APPLICATIONS

Device Description

The DG540, DG541, DG542 family of wideband switches offers true bidirectional switching of high frequency analog or digital signals with minimum signal crosstalk, low insertion loss, and negligible non-linearity distortion and group delay. Built on the Siliconix D/CMOS process, these "T" switches provide excellent off-isolation with a bandwidth of around 500 MHz (350 MHz for DG541). Silicon-gate D/CMOS processing also yields fast switching speeds.

An on-chip regulator circuit maintains TTL input compatibility over the whole operating supply voltage range, easing control logic interfacing.

Circuit layout is facilitated by the interchangeability of source and drain terminals.

Frequency Response

A single switch on-channel exhibits both resistance ($R_{DS(on)}$) and capacitance ($C_{S(on)}$). This RC combination has an attenuation effect on the analog signal – which is frequency dependent (like an RC low-pass filter). The - 3-dB bandwidth of the DG540 is typically 500 MHz (into 50 Ω). This measured figure of 500 MHz illustrates that the switch channel can not be represented by a two stage RC combination. The on capacitance of the channel is distributed along the on-resistance, and hence becomes a more complex multi stage network of R's and C's making up the total $R_{DS(on)}$ and $C_{S(on)}$. See Application Note AN502 for more details.

Off-Isolation and Crosstalk

Off-isolation and crosstalk are affected by the load resistance and parasitic inter-electrode capacitances. Higher off-isolation is achieved with lower values of R_L . However, low values of R_L increase insertion loss requiring gain adjustments down the line. Stray capacitances, even a fraction of 1 pF, can cause a large crosstalk increase. Good layout and ground shielding techniques can considerably improve your ac circuit performance.



APPLICATIONS

Power Supplies

A useful feature of the DG54X family is its power supply flexibility. It can be operated from a single positive supply (V+) if required (V- connected to ground).

Note that the analog signal must not exceed V- by more than - 0.3 V to prevent forward biasing the substrate p-n junction. The use of a V- supply has a number of advantages:

- 1. It allows flexibility in analog signal handling, i.e., with V- = -5 V and V+ = 12 V; up to \pm 5 V ac signals can be controlled.
- 2. The value of on capacitance $[C_{S(on)}]$ may be reduced. A property known as 'the body-effect' on the DMOS switch devices causes various parametric effects to occur. One of these effects is the reduction in C_{S(on)} for an increasing V body-source. Note, however, that to increase V- normally requires V+ to be reduced (since V+ to V- = 21 V max.). Reduction in V+ causes an increase in R_{DS(on)}, hence a compromise has to be achieved. It is also useful to note that optimum video linearity performance (e.g., differential phase and gain) occurs when V- is around - 3 V.
- 3. V- eliminates the need to bias the analog signal using potential dividers and large coupling capacitors.

Decoupling

It is an established RF design practice to incorporate sufficient bypass capacitors in the circuit to decouple the power supplies to all active devices in the circuit. The dynamic performance of the DG54X is adversely affected by poor decoupling of power supply pins. Also, of even more significance, since the substrate of the device is connected to the negative supply, adequate decoupling of this pin is essential.

Rules:

- 1. Decoupling capacitors should be incorporated on all power supply pins (V+, V-). (See Figure 7.)
- 2. They should be mounted as close as possible to the device pins.
- 3. Capacitors should have good high frequency characteristics - tantalum bead and/or monolithic ceramic types are adequate. Suitable decoupling capacitors are 1- to 10 µF tantalum bead, plus 10- to 100 nF ceramic.



DG540, DG541, DG542

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Figure 7. Supply Decoupling

- 3 \

Board Layout

 $C_1 = 10 \ \mu F$ Tantalum

C₂ = 0.1 µF Ceramic

PCB layout rules for good high frequency performance must be observed to achieve the performance boasted by the DG540. Some tips for minimizing stray effects are:

- 1. Use extensive ground planes on double sided PCB, separating adjacent signal paths. Multilayer PCB is even better.
- 2. Keep signal paths as short as practically possible, with all channel paths of near equal length.
- 3. Careful arrangement of ground connections is also very important. Star connected system grounds eliminate signal current flowing through ground path parasitic resistance from coupling between channels.

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APPLICATIONS

Figure 8 shows a 4 Channel video multiplexer using a DG540.





Figure 9 shows an RGB selector switch using two DG542s.



Figure 9. RGB Selector Using Two DG542s

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70055.

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SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012







PDIP: 16-LEAD







| | MILLIN | IETERS | INC | HES | |
|---|--------|--------|-------|-------|--|
| Dim | Min | Max | Min | Max | |
| Α | 3.81 | 5.08 | 0.150 | 0.200 | |
| A ₁ | 0.38 | 1.27 | 0.015 | 0.050 | |
| В | 0.38 | 0.51 | 0.015 | 0.020 | |
| B ₁ | 0.89 | 1.65 | 0.035 | 0.065 | |
| С | 0.20 | 0.30 | 0.008 | 0.012 | |
| D | 18.93 | 21.33 | 0.745 | 0.840 | |
| E | 7.62 | 8.26 | 0.300 | 0.325 | |
| E ₁ | 5.59 | 7.11 | 0.220 | 0.280 | |
| e ₁ | 2.29 | 2.79 | 0.090 | 0.110 | |
| e _A | 7.37 | 7.87 | 0.290 | 0.310 | |
| L | 2.79 | 3.81 | 0.110 | 0.150 | |
| Q ₁ | 1.27 | 2.03 | 0.050 | 0.080 | |
| S | 0.38 | 1.52 | .015 | 0.060 | |
| ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482 | | | | | |



Package Information Vishay Siliconix

PDIP: 20-LEAD





| | MILLIN | IETERS | INC | HES | |
|---|--------|---------------|-------|-------|--|
| Dim | Min | Max | Min | Max | |
| Α | 3.81 | 5.08 | 0.150 | 0.200 | |
| A ₁ | 0.38 | 1.27 | 0.015 | 0.050 | |
| В | 0.38 | 0.51 | 0.015 | 0.020 | |
| B ₁ | 0.89 | 1.65 | 0.035 | 0.065 | |
| С | 0.20 | 0.30 | 0.008 | 0.012 | |
| D | 24.89 | 26.92 | 0.980 | 1.060 | |
| Е | 7.62 | 8.26 | 0.300 | 0.325 | |
| E ₁ | 5.59 | 7.11 | 0.220 | 0.280 | |
| e ₁ | 2.29 | 2.79 | 0.090 | 0.110 | |
| e _A | 7.37 | 7.87 | 0.290 | 0.310 | |
| L | 3.175 | 3.81 | 0.123 | 0.150 | |
| Q 1 | 1.27 | 2.03 | 0.050 | 0.080 | |
| S | 1.02 | 2.03 | 0.040 | 0.080 | |
| ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5484 | | | | | |



Package Information Vishay Siliconix

PLCC: 20-LEAD





SIDEBRAZE: 16-LEAD





| | MILLIM | IETERS | INC | HES | |
|---|----------|--------|-----------|-------|--|
| Dim | Min | Max | Min | Max | |
| Α | 2.67 | 4.45 | 0.105 | 0.175 | |
| b | 0.38 | 0.53 | 0.015 | 0.021 | |
| b ₂ | 1.14 | 1.65 | 0.045 | 0.065 | |
| С | 0.20 | 0.30 | 0.008 | 0.012 | |
| D | 19.56 | 21.08 | 0.770 | 0.830 | |
| E | 7.11 | 7.87 | 0.280 | 0.310 | |
| е | 2.54 | BSC | 0.100 | BSC | |
| e _A | 7.62 BSC | | 0.300 BSC | | |
| L | 3.18 | 4.45 | 0.125 | 0.175 | |
| Q | 0.64 | 1.40 | 0.025 | 0.055 | |
| S ₂ | 0.25 | - | 0.010 | - | |
| S ₁ | 0.13 | _ | 0.005 | - | |
| ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5418 | | | | | |



SIDEBRAZE: 20-LEAD Meets MIL-STD-1835, D8, Configuration C





| | MILLIM | IETERS | INC | HES | | |
|----------------|---|--------------------|-------|-------|--|--|
| Dim | Min | Max | Min | Max | | |
| Α | 2.67 | 4.45 | 0.105 | 0.175 | | |
| b | 0.38 | 0.53 | 0.015 | 0.021 | | |
| b ₂ | 1.14 | 1.65 | 0.045 | 0.065 | | |
| С | 0.20 | 0.30 | 0.008 | 0.012 | | |
| D | 24.89 | 26.16 | 0.980 | 1.030 | | |
| E | 7.11 | 7.87 | 0.280 | 0.310 | | |
| е | 2.54 | 2.54 BSC 0.100 BSC | | | | |
| e _A | 7.62 | BSC | 0.300 | BSC | | |
| L | 3.18 | 4.45 | 0.125 | 0.175 | | |
| Q | 0.64 | 1.40 | 0.025 | 0.055 | | |
| S ₂ | 0.25 | - | 0.010 | - | | |
| S ₁ | 0.13 | - | 0.005 | - | | |
| | ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5309 | | | | | |

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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